Quad 8-Bit Nonvolatile DACPOT™ Electronic Potentiometer With a Mute Control Input

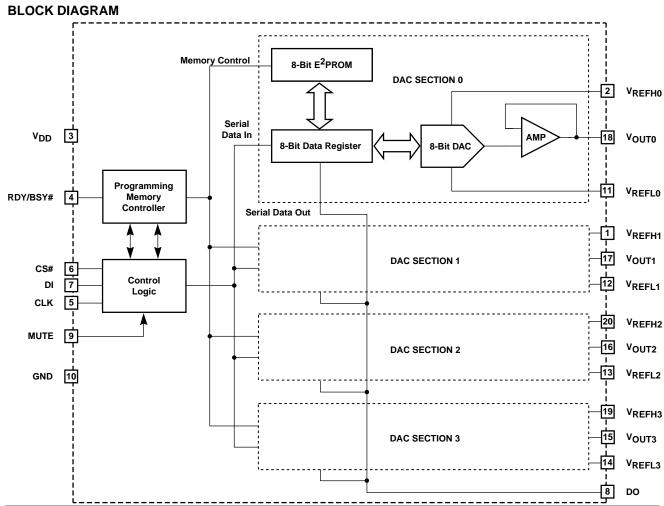
FEATURES

- Four 8-Bit DACs
 - Differential Non-linearity: ±0.5LSB max
 - Integral Non-Linearity Error: ±1LSB max
- Each DAC has Independent Reference Inputs
 - Output Buffer Amplifiers Swing Rail-to-Rail
 - Ground to V_{DD} Reference Input Range
- Each DAC's Digital Inputs Maintained in EEPROM
- Power-On Reset Reloads Registers with Nonvolatile Data
- Simple Serial Interface for Reading and Writing DAC values, SPI™ and QSPI™ compatible.
- Fully operational from 2.7V to 5.5V
- Low Power, 4mW max at +5V

OVERVIEW

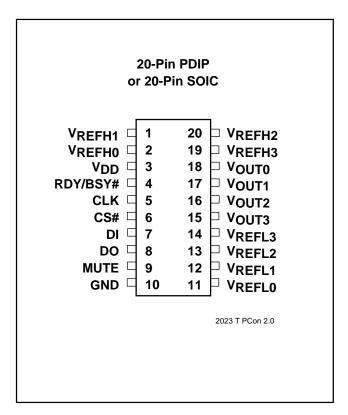
The S9418 DACPOT™ is a serial input, voltage output, quad 8-bit digital to analog converter (DAC). The S9418 operates from a single 2.7V to 5.5V supply. Internal precision buffers swing rail-to-rail and the reference input range includes both ground and the positive supply.

The S9418 integrates four 8-bit DACs and their associated circuits which include; an enhanced unity gain operational amplifier output, an 8-bit data latch, an 8-bit nonvolatile register and an industry standard serial interface for reading and writing data to the DACs' data latches and registers. The DACs are independently programmable and each has its own electrically isolated Vreference inputs.





PINOUT and SIGNAL DEFINITION



The analog outputs of the S9418 can be programmed to any one of 256 individual voltage steps. Each step value is $1/256^{th}$ of the voltage differential between V_{REFH} and V_{REFL} of the respective DAC. Once programmed these settings can be retained in nonvolatile memory during all power conditions and will be automatically recalled upon a power-up sequence. Each DAC can be independently read without affecting the output voltage during the read cycle. In addition each output can be adjusted an unlimited number of times without altering the value stored in the nonvolatile memory.

DEVICE OPERATION

Analog Section

The S9418 is an 8-bit, voltage output digital-to-analog converter (DAC). The DAC consists of a resistor network that converts 8-bit digital inputs into equivalent analog output voltages in proportion to the applied reference voltage.

Reference inputs

The voltage differential between the V_{REFL} and V_{REFH} inputs sets the full-scale output voltage for its respective DAC. V_{REFL} must be equal to or greater than ground (positive voltage). V_{REFH} must be greater (more positive) than V_{REFL} or equal to V_{DD} .

Pin	Name	Function		
1, 2 19, 20	V _{REFH}	Vreference High: VREFH - VDD > VREFL		
3	V_{DD}	Power Supply Voltage		
4	RDY/ BSY#	Ready/Busy#: open drain output indicating status of nonvolatile write operations		
5	CLK	Clock Input Pin: used for serial data communication		
6 CS#		Chip Select: When high deselects the device and places it in a low power mode		
7	DI	Data Input: serial data input pin		
8	DO	Data Output: serial data output pin		
9	MUTE	When active forces V _{OUT} to V _{REFL}		
10	GND	Power Supply Ground		
11, 12 13, 14	V_{REFL}	Vreference Low		
15, 16 17, 18	V _{OUT}	DAC Output: buffered D to A converter output		

Output Buffer Amplifiers

The voltage outputs are from precision unity-gain followers that can slew up to $1V/\mu s$. The outputs can swing from V_{REFL} to V_{REFH} . With a 0V to 5V output transition the amplifier outputs typically settle to 1LSB in 40 μs .

DIGITAL INTERFACE

The S9418 employs a common 4-wire serial interface. It is comprised of a Clock (CLK), Chip Select (CS#), Data input (DI) and Data output (DO). Data is clocked into the device on the clock's rising edge and out of the device on the clock's falling edge. Data is shifted in and out MSB first. DO only becomes active after the device has been selected <u>and</u> after a valid read command and address has been received.

All data transfers are initiated after CS# goes low and a logic '1' is clocked into the device. This first data transfer is the start bit and must precede all operations. Following the start bit are two command bits used to specify which of four commands to execute. The next two bits are the address bits used to select one of the four DACs. The action of the next eight clock cycles will be dependent upon the command issued.



Start	C ₁	C _o	A ₁	A ₀	Command		
1	0	0	Α	Α	NV Write Enable		
1	0	1	Α	Α	Write — Data In		
1	1	0	Α	Α	Read — Data Out		
1	1	1	A	Α	Recall		

TABLE 1.

Internally there are four DACs and associated with each are two registers. There is one data register that is used by the DAC to hold the digital value it converts. There is also one nonvolatile register that holds the default value that can be recalled into the data register during power-up or by executing the Recall command.

READ

Read operations are initiated by taking CS# low and clocking in a start bit followed by the read command and the address of the data register to be read. The next eight clocks will output on the DO pin the contents of the

selected data register. This read will not affect the contents of the register or the output of the DAC. Refer to Figure 1 for an illustration of the sequence of bus conditions for a read operation.

WRITE

Write operations are initiated by taking CS# low and clocking in a start bit followed by the write command and the address of the data register to be written. This action is followed by the host clocking eight bits of data into the register, MSB first. The output of the selected DAC will change as the last bit is clocked into the device. At this point the clock counter will reset the command register, requiring a full sequence to be initiated in order to write to the DAC again. Refer to Figure 2 for an illustration of the sequence of bus conditions for a write operation.

NOTE: This write operation does not affect the contents of the nonvolatile register. Therefore, the nonvolatile register can contain the power-on default settings (e.g. volume), and the write DAC command can be used to make situational adjustments.

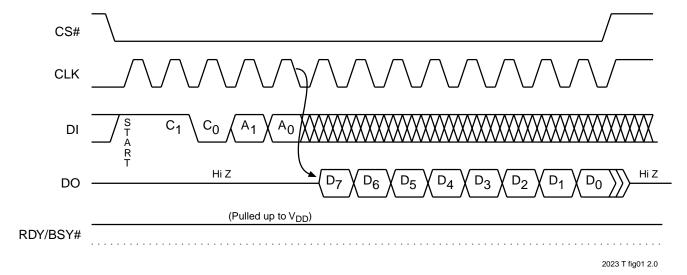


FIGURE 1. READ SEQUENCE

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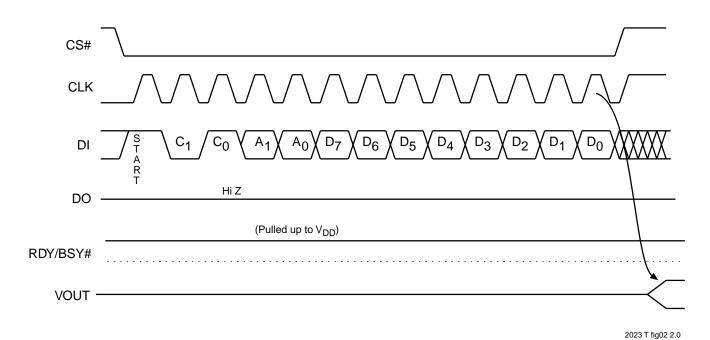
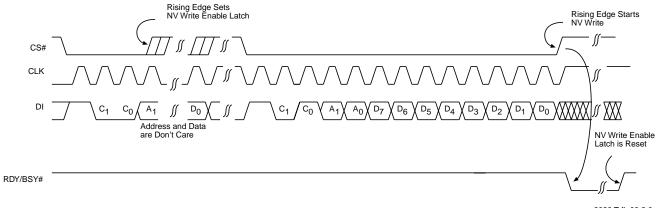


FIGURE 2. WRITE SEQUENCE



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FIGURE 3. NONVOLATILE WRITE SEQUENCE

NONVOLATILE WRITE

A nonvolatile write is a two step operation: it is initiated by taking CS# low and clocking in a start bit followed by the NV Write Enable command. At this point the host can take CS# back high or continue clocking in data. This data is don't care and will be ignored by the S9418.

Next, the host takes CS# low again and issues a write command and address and then clocks in the eight data bits to be programmed. The host will then bring CS# high and the data will be latched into the data register and a nonvolatile write operation will commence.

The status of the nonvolatile write can be monitored on the RDY/BSY# pin. A logic low indicates the write is still in progress and the S9418 will not be accessible to the host; a logic high indicates the write has completed and the S9418 is ready for the next command. Refer to Figure 3 for an illustration of the sequence of bus conditions for a nonvolatile write operation.



RECALL COMMAND

The recall command will retrieve data from the selected nonvolatile register and write it into the data register of the associated DAC. This operation is initiated by taking CS# low and clocking in a start bit followed by the recall command and the address of the nonvolatile register to be recalled. The eight bits of data are don't care, so CS# can be taken high any time after the address bits are clocked in. Refer to Figure 4 for an illustration of the sequence of bus conditions for a Recall operation.

Power-On Recall

Whenever the S9418 is powered on, the V_{OUT} values will be returned to the analog equivalent of the data byte stored in the nonvolatile register.

MUTE Operation

The MUTE input is active high. Whenever the input is low the V_{OUT} will reflect the value in the data register. If MUTE is driven high the V_{OUT} outputs will be switched to $V_{\text{REFL}}.$ Releasing the MUTE input returns the V_{OUT} outputs to the analog equivalent of the data register contents.

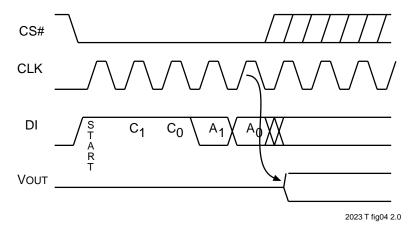


FIGURE 4. RECALL COMMAND SEQUENCE



ABSOLUTE MAXIMUM RATINGS

V _{DD} to GND	0.5V to +7V
Digital Inputs to Gnd	0.5V to V _{DD} +0.5V
Analog Inputs to ground	0.5V to V _{DD} +0.5V
Digital Outputs to Gnd	0.5V to V _{DD} +0.5V
Analog Outputs to Gnd	0.5V to V _{DD} +0.5V
Temperature Under Bias	55°C to +125°C
Storage Temperature	65°C to +150°C
Lead Soldering (10 Sec Max)	300°C

Stresses listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.

RECOMMENDED OPERATING CONDITIONS

Condition	Min	Max
Temperature	-40°C	+85°C
V_{DD}	+2.7V	+5.5V

2023 PGM T2 1.1

RELIABILITY CHARACTERISTICS (over recommended operating conditions unless otherwise specified)

Symbol	Parameter	Min	Max	Unit
V_{ZAP}	ESD Susceptibility	2000		V
I _{LTH}	Latch-up	100		mA
T_{DR}	Data Retention	100		Years
N _{END}	Endurance	1,000,000		Storage Cycles

DC ELECTRICAL CHARACTERISTICS (over recommended operating conditions unless otherwise specified)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DD}	Supply current during store (note 1)	CS = V _{IL}		1.8	3.0	mA
I _{SB}	Standby supply current	CS = V _{IH}		260	500	μΑ
I _{IH}	Input leakage current	$V_{IN} = V_{DD}$		<1	10	μA
I	Input leakage current	$V_{IN} = 0V$		<1	-10	μΑ
\/	High level input voltage	4.5V ≤ VCC ≤ 5.5V	2		V _{DD}	V
V _{IH}		VCC ≤ 4.5V	$0.9 \times V_{CC}$		V _{DD}	V
V	Low level input voltage	4.5V ≤ VCC ≤ 5.5V	0		0.8	V
V _{IL}		VCC ≤ 4.5V	0		$0.1 \times V_{CC}$	V
V _{OH}	High level output voltage	IOH = -400μA	V _{DD} - 0.3			V
V _{OL}	Low level output voltage	IOL = 1mA, V _{DD} = 5V; IOL = 0.4mA, V _{DD} = 2.7V			0.4	V

Note 1: I_{DD} is the supply current drawn while the EEPROM is being updated.

Typical $T_A = 25^{\circ}C$ and $V_{CC} = 5.0V$.



AC ELECTRICAL CHARACTERISTICS

 V_{DD} = +4.5V to +5.5V, V_{REFH} = V_{DD} , V_{REFL} = 0V, T_{A} = -40°C to +85°C, unless otherwise specified

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
f _C	Clock Frequency		DC		1	MHz
tWH	Minimum CLK High Time		500			ns
t _{WL}	Minimum CLK Low Time		300			ns
tCS	Minimum CS High Time		150			ns
tcss	CS Setup Time		100			ns
^t CSH	CS Hold Time		0			ns
^t SU	Data In Setup Time	$C_L = 100pF$	50			ns
t _H	Data In Hold Time	See Note 1	50			ns
ty	Output Valid Time				150	ns
tHO	Data Out Hold Time		0			ns
t _{DIS}	Output Disable Time			400		ns
^t BUSY	Write Cycle Time			3.3	5	ms

Notes:

1. All timing measurements are defined at the point of signal crossing $V_{\mbox{\scriptsize DD}}/2$.

2023 PGM T5 1.1

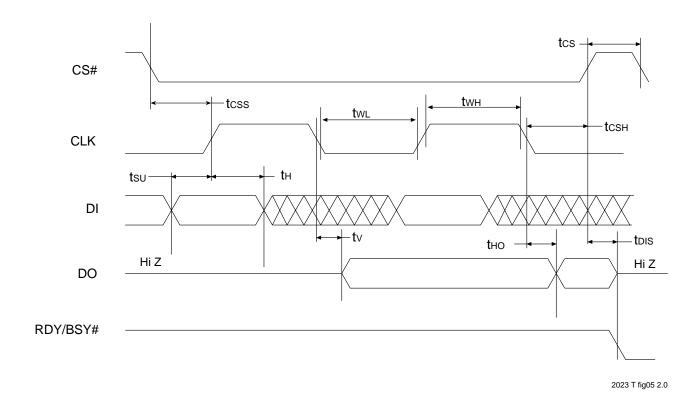


FIGURE 5. AC TIMING DIAGRAM



DAC ELECTRICAL CHARACTERISTICS

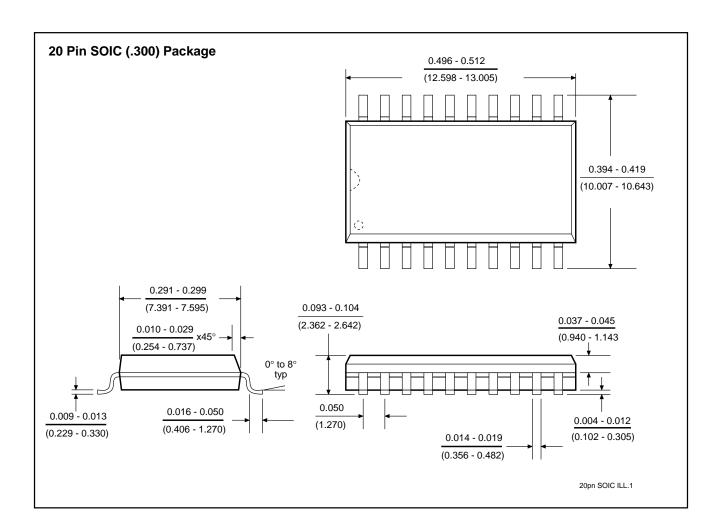
 V_{DD} = 2.7V to 5.5V, V_{REFH} = VDD, V_{REFL} = 0V, T_{A} = -40°C to 85°C, unless otherwise specified

Property	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Acquirect	INL	Integral non-linearity	$I_{LOAD} = 100 \mu A$		0.5	±1	LSB
Accuracy	DNL	Differential non-linearity	$I_{LOAD} = 100\mu A \text{ (note 1)}$		0.1	±0.5	LSB
	V_{REFH}	Input voltage		V_{REFL}			V
	V_{REFL}	Input voltage		GND			V
References	R _{IN}	$V_{\scriptscriptstyle REFH}$ to $V_{\scriptscriptstyle REFL}$ resistance			40k		Ω
	TCR _{IN}	Temp. coefficient of R _{IN}			300	600	ppm/ºC
	ΔR_{IN}	Input resistance match			±0.5	±1	%
	G_{EFS}	Full-scale gain error	D = FF _{HEX}			±1	LSB
	V _{OUT} ZS	Output offset voltage	D = 00 _{HEX}	0	2.5	5	mV
	TCV _{OUT}	V_{OUT} temp. coeffiecient	$V_{DD} = 5V$, $I_{LOAD} = 50\mu A$ (note 1)			50	μV/ºC
	I _L	Amp output load current		-200		1000	μΑ
Analog	R _{OUT}	Amp output resistance	$V_{DD} = V_{REFH}$ 5V 3V		10 20		Ω
Output	PSRR	Power supply rejection	$I_{LOAD} = 10\mu A$			1	LSB/V
	t _s	DAC settling time to 1LSB	10pF 5V 10pF 3V		36 27		µs µs
	e _N	Amp output noise	$f = 1kHz, V_{DD} = 5V$		90		nV√Hz
	THD	Total harmonic distortion	$V_{REFH} = 2.5V, V_{DD} = 5V,$ f = 1kHz, $V_{IN} = 1V_{RMS}$		0.08		%
	BW	Bandwidth –3dB	$V_{REFH} = 2.5V, V_{DD} = 5V, V_{IN} = 100 \text{mV}_{RMS}$		300		kHz

Note 1: Guaranteed but not tested.

Typical $T_A = 25^{\circ}C$ and $V_{CC} = 5.0V$.





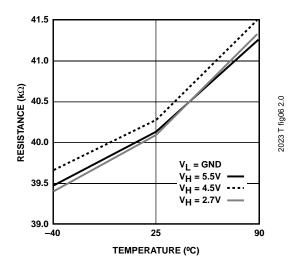
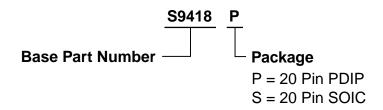


FIGURE 6. $\rm V_L$ TO $\rm V_H$ END-TO-END RESISTANCE OVER TEMPERATURE



ORDERING INFORMATION



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